

◇ STRUCTURE Silicon Monolithic Integrated Circuit

◇ PRODUCT SPI BUS 2Kbit (256 × 8bit) EEPROM

◇ PART NUMBER BR25L020-W Series

PART NUMBER	PACKAGE
BR25L020F-W	SOP8
BR25L020FJ-W	SOP-J8
BR25L020FV-W	SSOP-B8
BR25L020FVT-W	TSSOP-B8
BR25L020FVM-W	MSOP8
BR25L020FVJ-W	TSSOP-B8J

◇ FEATURES  
 Serial Peripheral Interface  
 Single power supply (1.8V~5.5V)  
 1,000,000 erase/write cycles endurance

◇ ABSOLUTE MAXIMUM RATING (Ta=25°C)

Parameter	Symbol	Rating	Unit
Supply Voltage	Vcc	-0.3~6.5	V
Power Dissipation	Pd	450 (BR25L020F-W) *1	mW
		450 (BR25L020FJ-W) *2	
		300 (BR25L020FV-W) *3	
		330 (BR25L020FVT-W) *4	
		310 (BR25L020FVM-W) *5	
		310 (BR25L020FVJ-W) *6	
Storage Temperature	Tstg	-65~125	°C
Operating Temperature	Topr	-40~85	°C
Terminal Voltage	—	-0.3~Vcc+0.3	V

\* Degradation is done at 4.5mW/°C(\*1,\*2), 3.0mW/°C(\*3), 3.3mW/°C(\*4),  
 3.1mW/°C(\*5,\*6) for operation above 25°C

◇ RECOMMENDED OPERATING CONDITION

Parameter	Symbol	Rating	Unit
Supply Voltage	Vcc	1.8~5.5	V
Input Voltage	VIN	0~Vcc	V

Status of this document

The Japanese version of this document is the formal specification.

A customer may use this translation version only for a reference to help reading the formal version.

If there are any differences in translation version of this document, formal version takes priority.

◇MEMORY CELL CHARACTERISTICS( $T_a=25^\circ C$ ,  $V_{cc}=1.8 \sim 5.5V$ )

Parameter	Specification			Unit
	Min.	Typ.	Max.	
Write/Erase Cycle *1	1,000,000	—	—	Cycle
Data Retention *1	40	—	—	Year

○Initial Data: Memory array FFh, Status Register BP1:0, BP0:0

\*1 Not 100% TESTED

## ◇ DC OPERATING CHARACTERISTICS

(Unless otherwise specified  $T_a=-40 \sim 85^\circ C$ ,  $V_{cc}=1.8 \sim 5.5V$ )

Parameter	Symbol	Specification			Unit	test condition
		Min.	Typ.	Max.		
"H" Input Voltage1	VIH1	0.7xVcc	—	Vcc+0.3	V	1.8V $\leq$ Vcc $\leq$ 5.5V
"L" Input Voltage1	VIL1	-0.3	—	0.3xVcc	V	1.8V $\leq$ Vcc $\leq$ 5.5V
"L" Output Voltage1	VOL1	0	—	0.4	V	IOL=2.1mA ( $V_{cc}=2.5V \sim 5.5V$ )
"L" Output Voltage2	VOL2	0	—	0.2	V	IOL=150 $\mu$ A ( $V_{cc}=1.8V \sim 5.5V$ )
"H" Output Voltage1	VOH1	Vcc-0.5	—	Vcc	V	IOH=0.4mA ( $V_{cc}=2.5V \sim 5.5V$ )
"H" Output Voltage2	VOH2	Vcc-0.2	—	Vcc	V	IOH=100 $\mu$ A ( $V_{cc}=1.8V \sim 5.5V$ )
Input Leakage Current	ILI	-1	—	1	$\mu$ A	VIN=0V $\sim$ Vcc
Output Leakage Current	ILO	-1	—	1	$\mu$ A	VOUT=0V $\sim$ Vcc, CS=Vcc
Operating Current Write	ICC1	—	—	1	mA	$V_{cc}=1.8V$ , fSCK=2MHz, tE/W=5ms Byte Write, Page Write, Write Status Register
	ICC2	—	—	2	mA	$V_{cc}=2.5V$ , fSCK=5MHz, tE/W=5ms Byte Write, Page Write, Write Status Register
	ICC3	—	—	3	mA	$V_{cc}=5.5V$ , fSCK=5MHz, tE/W=5ms Byte Write, Page Write, Write Status Register
Operating Current Read	ICC4	—	—	1.5	mA	$V_{cc}=2.5V$ , fSCK=5MHz Read, Read Status Register
	ICC5	—	—	2	mA	$V_{cc}=5.5V$ , fSCK=5MHz Read, Read Status Register
Standby Current	ISB	—	—	2	$\mu$ A	$V_{cc}=5.5V$ CS=HOLD=WP=Vcc SCK=SI=Vcc or GND, SO=OPEN

○This product is not designed for protection against radioactive rays.

## ◇ AC OPERATING CHARACTERISTICS

(Unless otherwise specified  $T_a=-40 \sim 85^\circ C$ ,  $C_L=100pF$ )

Parameter	Symbol	1.8V $\leq$ Vcc $\leq$ 2.5V			2.5V $\leq$ Vcc $\leq$ 5.5V			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
SCK clock Frequency	fSCK	—	—	2	—	—	—	5 MHz
SCK High Time	tSCKWH	200	—	—	85	—	—	ns
SCK Low Time	tSCKWL	200	—	—	85	—	—	ns
CS High Time	tCS	200	—	—	85	—	—	ns
CS Setup Time	tCSS	200	—	—	90	—	—	ns
CS Hold Time	tCSH	200	—	—	85	—	—	ns
SCK Setup Time	tSCKS	200	—	—	90	—	—	ns
SCK Hold Time	tSCKH	200	—	—	90	—	—	ns
SI Setup Time	tDIS	40	—	—	20	—	—	ns
SI Hold Time	tDIH	50	—	—	40	—	—	ns
Output Data Delay Time1	tPD1	—	—	150	—	—	70	ns
Output Data Delay Time2 (C <sub>L</sub> =30pF)	tPD2	—	—	145	—	—	55	ns
Output Hold Time	tOH	0	—	—	0	—	—	ns
Output Disable Time	tOZ	—	—	250	—	—	100	ns
Clock High Setup Time before HOLD Active	tHFS	120	—	—	60	—	—	ns
Clock Low Hold Time after HOLD Active	tHFH	90	—	—	40	—	—	ns
Clock High Setup Time before HOLD not Active	tHRS	120	—	—	60	—	—	ns
Clock Low Hold Time after HOLD not Active	tHRH	140	—	—	70	—	—	ns
HOLD to Output High-Z	tHOZ	—	—	250	—	—	100	ns
HOLD to Output Valid	tHPD	—	—	150	—	—	70	ns
SCK Rise Time *1	tRC	—	—	1	—	—	1	$\mu$ s
SCK Fall Time *1	tFC	—	—	1	—	—	1	$\mu$ s
Output Rise Time *1	tRO	—	—	100	—	—	50	ns
Output Fall Time *1	tFO	—	—	100	—	—	50	ns
Write Cycle Time	tE/W	—	—	5	—	—	5	ms

\*1 Not 100% TESTED

## ◇ BLOCK DIAGRAM

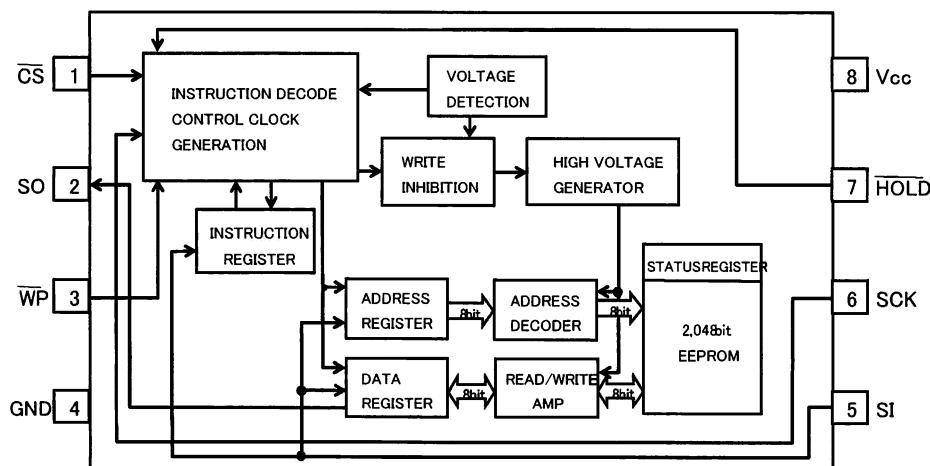


Fig.1 BLOCK DIAGRAM

## ◇ PIN No. / PIN NAME

PIN No.	PIN NAME
1	CS
2	SO
3	WP
4	GND
5	SI
6	SCK
7	HOLD
8	Vcc

### ◇NOTES FOR POWER SUPPLY

In order to prevent an inadvertent write, the device has the feature of P.O.R.

After the power is on, the device is in the write disable mode. P.O.R. works only during power up. The noise may force the device write enable mode with  $\overline{CS} = "H"$  during power ON/OFF. In the case of power up, keep the following conditions to ensure to make the function of P.O.R.

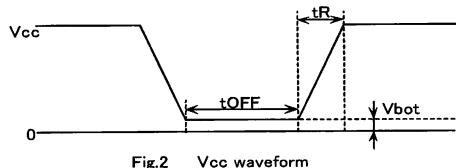


Fig.2 Vcc waveform

### ◇RECOMMENDED CONDITIONS OF tR, tOFF, Vbot

tR	tOFF	Vbot
Below 10ms	Above 10ms	Below 0.3V
Below 100ms	Above 10ms	Below 0.2V

Please keep  $\overline{CS}$  "H" during power ON/OFF.

The device is an active state during  $\overline{CS}$  is low. The extraordinary function or data collaption may occur because of noise etc., if power-up is done with  $\overline{CS}$  "L". In order to prevent above errors from happening, keep  $\overline{CS}$  "H" ( $=Vcc$ ) during power ON. (The device does not receive any command during  $\overline{CS}$  is high.)

It may continue at low Vcc by capacitance of Vcc line during power off.

Please keep  $\overline{CS}$  "H" during power off because of the device may make malfunction and inadvertent write.

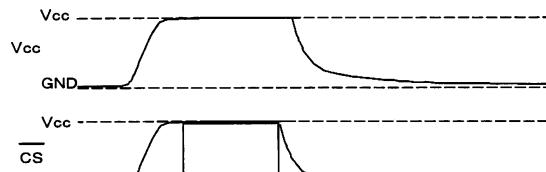


Fig.3  $\overline{CS}$  TIMING DURING POWER ON/OFF

(Good example)

$\overline{CS}$  follows Vcc. ( $\overline{CS}$  is pull up to Vcc)

(Bad example)

$\overline{CS}$  is low during power ON/OFF.

Please take more than 10ms between power ON and power OFF, or the internal circuit is not always reset.

### ◇CAUTIONS ON USE

#### (1) Absolute maximum ratings

If the absolute maximum ratings such as impressed voltage and operating temperature range and so forth are exceeded, LSI may be destructed. Do not impress voltage and temperature exceeding the absolute maximum ratings. In the case of fear exceeding the absolute maximum ratings, take physical safety countermeasures such as fuses, and see to it that conditions exceeding the absolute maximum ratings should not be impressed to LSI.

#### (2) GND electric potential

Set the voltage of GND terminal lowest at any action condition. Make sure that each terminal voltage is lower than that of GND terminal.

#### (3) Heat design

In consideration of permissible dissipation in actual use condition, carry out heat design with sufficient margin.

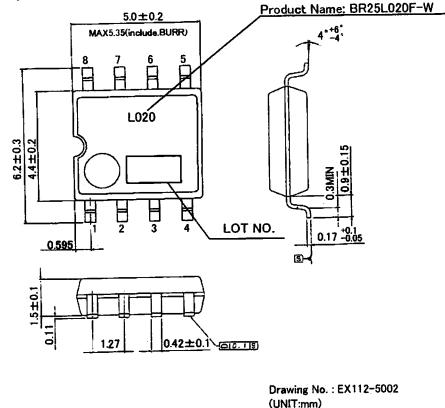
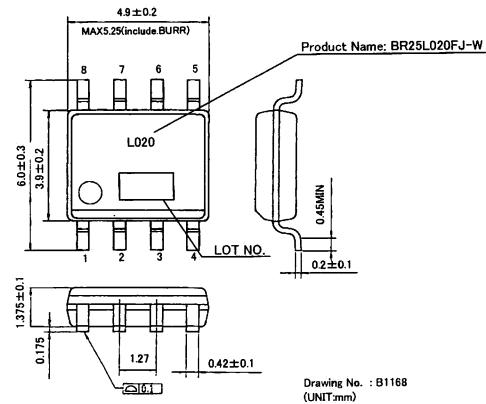
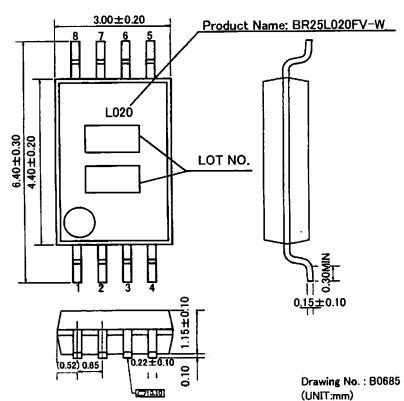
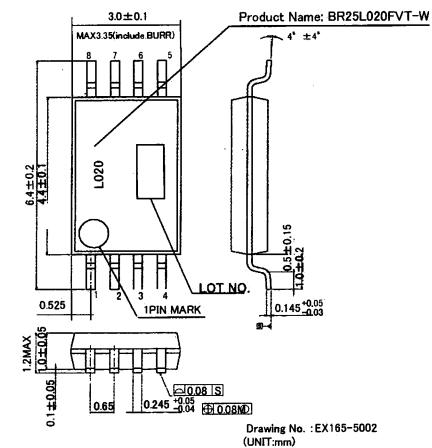
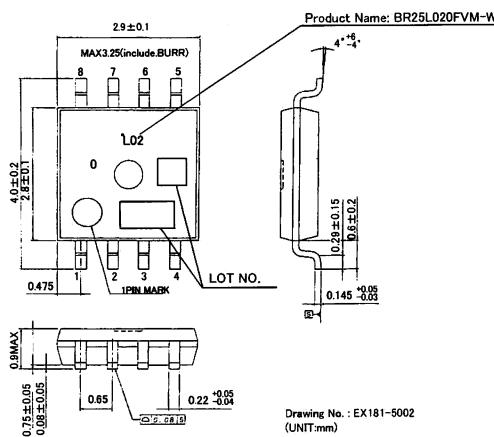
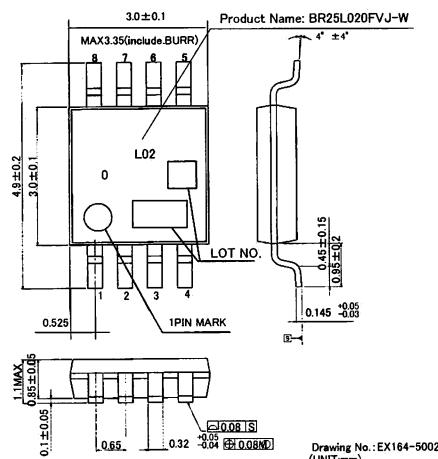
#### (4) Terminal to terminal shortcircuit and wrong packaging

When to package LSI onto a board, pay sufficient attention to LSI direction and displacement. Wrong packaging may destruct LSI. And in the case of shortcircuit between LSI terminals and terminals and power source, terminal and GND owing to foreign matter, LSI may be destructed.

#### (5) Strong electromagnetic field

Use in a strong electromagnetic field may cause malfunction, therefore, evaluated design sufficiently.

## ◇PHYSICAL DIMENSION

Fig4-(a) PHYSICAL DIMENSION  
SOP8(BR25L020F-W)Fig4-(b) PHYSICAL DIMENSION  
SOP-J8(BR25L020FJ-W)Fig4-(c) PHYSICAL DIMENSION  
SSOP-B8(BR25L020FV-W)Fig4-(d) PHYSICAL DIMENSION  
TSSOP-B8(BR25L020FVT-W)Fig4-(e) PHYSICAL DIMENSION  
MSOP8(BR25L020FVM-W)Fig4-(f) PHYSICAL DIMENSION  
TSSOP-B8J(BR25L020FVJ-W)

## Appendix

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